

EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	4	((AKI RA) near2 (BANDOH)). INV.	US-PGPUB; USPAT	OR	OFF	2010/06/18 12:43
L2	47	((HI ROMI TSU) near2 (SAKAI)). INV.	US-PGPUB; USPAT	OR	OFF	2010/06/18 13:11
L3	14	((MASATO) near2 (KOBAYAKAWA)).INV.	US-PGPUB; USPAT	OR	OFF	2010/06/18 13:12
L4	19	((MINEO) near2 (OKUYAMA)). INV.	US-PGPUB; USPAT	OR	OFF	2010/06/18 13:13
L5	15	((HI DEKI) near2 (TOMOZAWA)).INV.	US-PGPUB; USPAT	OR	OFF	2010/06/18 13:13
L6	60	((HI SAYUKI) near2 (MIKI)). INV.	US-PGPUB; USPAT	OR	OFF	2010/06/18 13:14
L7	3	((SYUNJI) near2 (HORI KAWA)).INV.	US-PGPUB; USPAT	OR	OFF	2010/06/18 13:14
L8	3	((SYUNJI) near2 (HORI KAWA)).INV.	US-PGPUB; USPAT	OR	OFF	2010/06/18 13:15
L9	37	((TETSUO) near2 (SAKURAI)). INV.	US-PGPUB; USPAT	OR	OFF	2010/06/18 13:16
L10	4	((AKI RA) near2 (BANDOH)). INV.	US-PGPUB; USPAT	OR	OFF	2010/06/18 13:17
L11	2821	257/79.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/18 13:19
L12	89	l11 and (GaN III\$1V (III near2 nitride)) and ((germanium Ge) near4 (dop\$3 impurity))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/18 13:22
L13	58	l11 and (GaN III\$1V (III near2 nitride)) and ((germanium Ge) near4 (dop\$3 impurity)) and (@ad< "20040427" or @rlad< "20040427")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/18 13:23
L14	52	257/13.ccls. and (GaN III\$1V (III near2 nitride)) and ((germanium Ge) near4 (dop \$3 impurity)) and (@ad< "20040427" or @rlad< "20040427")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/18 13:24

L15	39	257/102.ccls. and (GaN III\$1V (III near2 nitride)) and ((germanium Ge) near4 (dop \$3 impurity)) and (@ad<"20040427" or @rlad<"20040427")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/18 13:24
L16	145	257/103.ccls. and (GaN III\$1V (III near2 nitride)) and ((germanium Ge) near4 (dop \$3 impurity)) and (@ad<"20040427" or @rlad<"20040427")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/18 13:25
L17	76	111 and (GaN III\$1V (III near2 nitride)) and ((germanium Ge) near4 (dop\$3 impurity)) and (@ad<"20060712" or @rlad<"20060712")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/18 13:25
L18	76	257/79.ccls. and (GaN III\$1V (III near2 nitride)) and ((germanium Ge) near4 (dop \$3 impurity)) and (@ad<"20060712" or @rlad<"20060712")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/18 13:26
L19	62	257/13.ccls. and (GaN III\$1V (III near2 nitride)) and ((germanium Ge) near4 (dop \$3 impurity)) and (@ad<"20060712" or @rlad<"20060712")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/18 13:26
L20	47	257/102.ccls. and (GaN III\$1V (III near2 nitride)) and ((germanium Ge) near4 (dop \$3 impurity)) and (@ad<"20060712" or @rlad<"20060712")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/18 13:26
L21	179	257/103.ccls. and (GaN III\$1V (III near2 nitride)) and ((germanium Ge) near4 (dop \$3 impurity)) and (@ad<"20060712" or @rlad<"20060712")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/18 13:26
L22	7	257/e33.03.ccls. and (GaN III \$1V (III near2 nitride)) and ((germanium Ge) near4 (dop \$3 impurity)) and (@ad<"20060712" or @rlad<"20060712")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/18 13:31
L23	74	257/e33.008.ccls. and (GaN III \$1V (III near2 nitride)) and ((germanium Ge) near4 (dop \$3 impurity)) and (@ad<"20060712" or @rlad<"20060712")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/18 13:31

L24	17	257/e33.028.ccls. and (GaN III \$1V (III near2 nitride)) and ((germanium Ge) near4 (dop \$3 impurity)) and (@ad<"20060712" or @rlad<"20060712")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/18 13:32
L25	41	438/47.ccls. and (GaN III \$1V (III near2 nitride)) and ((germanium Ge) near4 (dop \$3 impurity)) and (@ad<"20040427" or @rlad<"20040427")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/18 14:25
L26	0	438/438.ccls. and (GaN III \$1V (III near2 nitride)) and ((germanium Ge) near4 (dop \$3 impurity)) and (@ad<"20040427" or @rlad<"20040427")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/18 14:25
L27	3	438/689.ccls. and (GaN III \$1V (III near2 nitride)) and ((germanium Ge) near4 (dop \$3 impurity)) and (@ad<"20040427" or @rlad<"20040427")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/18 14:25
L28	46	438/46.ccls. and (GaN III \$1V (III near2 nitride)) and ((germanium Ge) near4 (dop \$3 impurity)) and (@ad<"20040427" or @rlad<"20040427")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/18 14:25
S1	4	("20030010993" "6252255"). PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/11 18:49
S2	1	"10585744"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/11 18:51
S3	96902	(III near nitride) or (III \$1nitride) or (III \$1V)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/11 20:26
S4	3425	(n\$1type or n\$1dop\$3) near4 (Germanium Ge)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/11 20:27

S5	177412	(pit or dislocation)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/11 20:28
S6	145542	dop\$3 with (high\$2 low\$2)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/11 20:29
S7	46391	dop\$3 with (high\$2 low\$2) with (concentration density)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/11 20:30
S8	64	S3 and S4 and S5 and S7	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/11 20:30
S9	30	S8 and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/11 20:32
S10	45	S5 and 257/101.ccls. and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/11 20:49
S11	55	S5 and 257/102.ccls. and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/11 21:03
S12	301	S5 and 257/103.ccls. and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/11 21:15
S13	78	S12 and pit	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/11 21:15

S14	18	("5091333" "5895706" "5927995" "6010937" "6015979" "6281524").PN. OR ("6555846").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/04/11 22:10
S15	1398	pioneer.asn. and pit	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/11 22:20
S16	37	pioneer.asn. and pit and LED	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/11 22:20
S17	101	dop\$3 with (high\$2 low\$2) with (GaN III\$1V) with (germanium Ge)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/22 00:30
S18	53	S17 and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 00:31
S19	54	(dop\$3 with (high\$2 low\$2) with (GaN III\$1V (III near2 nitride)) with (germanium Ge)) and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/22 00:35
S20	97043	(III near nitride) or (III \$1nitride) or (III\$1V)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/22 00:45
S21	3443	(n\$1type or n\$1dop\$3) near4 (Germanium Ge)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/22 00:45
S22	177753	(pit or dislocation)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/22 00:45

S23	46511	dop\$3 with (high\$2 low\$2) with (concentration density)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 00:45
S24	64	S20 and S21 and S22 and S23	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 00:45
S25	30	S24 and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 00:47
S26	285	257/94.cor. and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 00:55
S27	18	257/615.cor. and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 14:17
S28	5	("20020046693" "20030070607" "20030134493" "6447604" "6773504").PN. OR ("7288830").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/04/22 14:30
S29	317	257/615.ccls. and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 14:36
S30	4	257/e33.023.ccls. and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 15:59
S31	7	257/e29.087.ccls. and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 16:00

S32	347	257/616.ccls. and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 16:02
S33	337	S32 not S29	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 16:02
S34	542	high\$2 with low\$2 with dop\$3 with (germanium Ge)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 16:11
S35	1198	n\$1type with (group near2 III) with nitride	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 16:13
S36	94849	(pit or protrusion) near3 surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 16:14
S37	0	S34 and S35 and S36 and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 16:14
S38	609876	(pit or protrusion)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 16:14
S39	0	S34 and S35 and S38 and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 16:15
S40	0	S34 and S35 and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 16:16

S41	5015	high\$2 same low\$2 same dop \$3 same(germanium Ge)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 16:16
S42	0	S35 and S38 and S41 and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 16:17
S43	14	S35 and S41 and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 16:17
S44	97043	(III near nitride) or (III \$1nitride) or (III\$1V)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/22 16:45
S45	3443	(n\$1type or n\$1dop\$3) near4 (Germanium Ge)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/22 16:45
S46	46511	dop\$3 with (high\$2 low\$2) with (concentration density)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 16:45
S47	28	S44 and S45 and pit and S46	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 16:45
S48	9	S47 and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 16:46
S49	3854	(group near III near nitride near semiconductor) or (III-V near nitride near compound near semiconductor) or (GaN- based near2 semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/22 18:33

S50	94779	n-type near2 (layer or film or structure or region)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/22 18:33
S51	53954	(high\$2 near2 concentration) same (low\$2 near2 concentration)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/22 18:37
S52	2695	S50 same S51	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/22 18:42
S53	189	S50 same ((Ge near2 dop\$3) or (dop\$3 near Ge))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/22 18:44
S54	3398266	pits or holes or cavities or depressions or valley or trough or recess	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/22 18:45
S55	4	S49 and S52 and S53 and S54	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/22 18:47
S56	0	S55 and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 18:49
S57	14	S49 and S52 and S54	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/22 19:02
S58	55	S49 and S50 and S51 and S54	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/22 19:09

S59	22	S58 and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 19:12
S60	24362	(n-type near2 (layer or film or structure or region)) same concentration	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 19:17
S61	216	S49 and S60 and S54	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 19:18
S62	16	("20020123246" "20030070607" "20040169192" "20040206299" "20050156153" "20060046511" "6365921" "6555846").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 19:53
S63	28	("5886367" "5927995" "6072197" "6100545" "6130446").PN. OR ("6365921").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/04/22 20:04
S64	24	kawano.in. and (group near III)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/22 20:40
S65	0	("jp2003-017420").PN.	JPO; DERWENT	OR	OFF	2009/04/22 20:47
S66	0	("jp2003-17420").PN.	JPO; DERWENT	OR	OFF	2009/04/22 20:47
S67	0	("2003-17420").PN.	JPO; DERWENT	OR	OFF	2009/04/22 20:47
S68	4	("2003017420").PN.	JPO; DERWENT	OR	OFF	2009/04/22 20:47
S69	7	("20020053679" "20020136932" "5488233" "5740192" "6153894" "6462357" "6555846").PN. OR ("6943366").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/04/22 21:31
S70	2	("20040188691").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/22 21:35

S71	6	("6261931").PN. OR ("6462357").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/04/22 21:37
S72	53838	dislocation	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/22 21:41
S73	4	S49 and S52 and S53 and S72	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 21:42
S74	30	S49 and S50 and S51 and (dislocation dis\$1location)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/22 21:44
S75	14	S74 and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/22 21:44
S76	3	(bandoh near akira).in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/23 09:11
S77	2	("20040113166").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/23 09:19
S78	2	"7053420".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/23 09:22
S79	15	("20010050376" "20030085411" "20040048471" "5727015" "5779924" "6091083" "6091085" "6316785" "6617182" "6720586" "6940098").PN. OR ("7053420").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/04/23 09:22
S80	5	("20030218179" "20040113166" "6091085" "6531719" "6623998").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/04/23 09:28

S81	0	257/e33.033.ccls. and @ad<"20040427" and (pits or dislocation)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/23 09:31
S82	2	257/e33.033.ccls. and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/23 09:31
S83	4	257/e33.034.ccls. and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/23 09:32
S84	1477	257/79.ccls. and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/23 09:38
S85	687	257/79.cor. and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/23 09:39
S86	115	257/79.cor. and @ad<"20040427" and (pits or dislocation)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/23 09:40
S87	11	257/101.cor. and @ad<"20040427" and (pits or dislocation)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/23 10:01
S88	10	257/102.cor. and @ad<"20040427" and (pits or dislocation)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/23 10:03
S89	121	257/103.cor. and @ad<"20040427" and (pits or dislocation)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/23 10:05

S90	2	("20020123246").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/23 14:06
S91	37	("20020036286" "20020042159" "20020043890" "20030178634" "20040026704" "20040051105" "3909929" "4985113" "5332697" "5429954" "5633192" "5652438" "5717226" "5767581" "5786233" "5787104" "5804918" "5874747" "5880485" "5888886" "5900650" "5929466" "6030848" "6046464" "6090666" "6103604" "6172382" "6177684" "6191436" "6242328" "6261862" "6277665" "6355945" "6423984" "6429102" "6455337" "6465808").PN. OR ("6861270").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/04/23 14:40
S92	8	("4139858" "4862471" "5679152").PN. OR ("6103604").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/04/23 14:47
S93	1116	((dop\$3 impurity) with (high\$2 low\$2)) and (GaN III\$1V (III near2 nitride)) and (dop\$3 with (germanium Ge)) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/27 13:32
S94	263	S93 and (dislocation or pits)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/27 13:33
S95	149	S94 and (layered stack\$2)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/27 13:33
S96	28464846	((dop\$3 impurity) with (high\$2 low\$2) with (germanium Ge)) and (GaN III\$1V (III near2 nitride)) and (layered stack\$2) and pits @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/27 13:41

S97	12	((dop\$3 impurity) with (high\$2 low\$2) with (germanium Ge)) and (GaN III\$1V (III near2 nitride)) and (layered stack\$2) and pits and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/27 13:42
S98	137	((dop\$3 impurity) with (high\$2 low\$2) with (germanium Ge)) and (GaN III\$1V (III near2 nitride)) and (layered stack\$2) and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/27 13:44
S99	31	((dop\$3 impurity) with (high\$2 low\$2) with (germanium Ge)) and ((GaN III\$1V (III near2 nitride)) with (resist\$3 conduct \$5)) and (layered stack\$2) and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/27 14:09
S100	72	((GaN III\$1V (III near2 nitride)) same ((germanium Ge) near4 (dop\$3 impurity)) same ((high low) and (resist\$5 conduct\$5))) and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/27 14:18
S101	3862	(group near III near nitride near semiconductor) or (III-V near nitride near compound near semiconductor) or (GaN-based near2 semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/27 14:35
S102	94870	n-type near2 (layer or film or structure or region)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/27 14:35
S103	54023	(high\$2 near2 concentration) same (low\$2 near2 concentration)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/27 14:35
S104	30	S101 and S102 and S103 and (dislocation dis\$1location)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/27 14:35
S105	14	S101 and S102 and S103 and (dislocation dis\$1location) and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/27 14:38

S106	97115	(III near nitride) or (III \$1nitride) or (III\$1V)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/27 14:42
S107	3443	(n\$1type or n\$1dop\$3) near4 (Germanium Ge)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/27 14:42
S108	46561	dop\$3 with (high\$2 low\$2) with (concentration density)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/27 14:42
S109	28	S106 and S107 and pit and S108	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/27 14:42
S110	4565	S102 and S103 and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/27 14:43
S111	168	S110 and (dop\$3 near5 (ge Germanium))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/27 14:45
S112	6	S111 and S101	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/27 14:57
S113	5	("20030047744" "5889806" "6249534" "6252894" "6597716").PN. OR ("6822272").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/04/27 15:08
S114	47	S111 and (low near resistance)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/27 16:14

S115	2	"6462357".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/27 16:34
S116	6	("6261931").PN. OR ("6462357").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/04/27 16:46
S117	7	("20020053679" "20020136932" "5488233" "5740192" "6153894" "6462357" "6555846").PN. OR ("7172956").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/04/27 16:47
S118	6	("6261931").PN. OR ("6462357").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/04/27 17:30
S119	5	("20020046693" "20030070607" "20030134493" "6447604" "6773504").PN. OR ("7288830").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/04/27 17:52
S120	8	("20020123246" "20030070607" "20040169192" "20040206299" "20050156153" "20060046511" "6365921" "6555846").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/04/27 18:10
S121	28	("5886367" "5927995" "6072197" "6100545" "6130446").PN. OR ("6365921").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/04/27 18:20
S122	1	"20050104081"	US-PGPUB; USPAT; USOCR	OR	OFF	2009/04/29 14:20
S123	2	("20070029560").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/04 12:40
S124	14	("20040211969" "20050062399" "20050224829" "20050236630" "20060273324" "20070018183" "20070170448").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/04 12:42
S125	2	("20020123246").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/04 12:54

S126	0	("(Asai near Keiichiro).in. and (III near nitride)").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/04 13:27
S127	50	(Asai near Keiichiro).in. and (III near nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/04 13:27
S128	50	(Asai near Keiichiro).in. and (III near nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/04 13:27
S129	228	(NGK near INSULATORS).asn. and(III near nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/04 13:31
S130	111	(NGK near INSULATORS).asn. and(III near nitride) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/04 13:32
S131	5	("20020061655" "20020155649" "20020190275" "5549951" "6508878").PN. OR ("6749957").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/04 13:35
S132	4	"2003017420"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/04 17:39
S133	289	(KAWANO near KENJI).in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/04 17:40
S134	0	(KAWANO near KENJI).in. and (III near nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/04 17:40

S135	0	(KAWANO near KENJI).in. and (GaN)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/04 17:41
S136	1	(KAWANO near KENJI).in. and Nichia	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/04 17:41
S137	1	(KAWANO near KENJI).in. and (gallium near nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/04 17:41
S138	97235	(III near nitride) or (III \$1nitride) or (III\$1V)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/05 10:17
S139	130	S138 and ((carrier near gas) with flow with (high\$2 low\$2))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/05 10:17
S140	97235	(III near nitride) or (III \$1nitride) or (III\$1V)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/05 16:29
S141	59	S140 and (((("carrier gas" or "inert gas") near4 flow) with (dop\$3 impurity)) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/05 16:29
S142	0	S140 and (((("carrier gas" or "inert gas") with flow with different) with (dop\$3 impurity)) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/05 17:06
S143	96	S140 and (((("carrier gas" or "inert gas") with flow) with (dop\$3 impurity)) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/05 17:06

S144	94	((("carrier gas" or "inert gas") same (high near2 concentration) same (low near concentration)) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/05 17:23
S145	5	((("carrier gas" or "inert gas") same (high near2 concentration) same (low near concentration) same (flow near2 rate)) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/05 17:26
S146	4	(effect with carrier with gas with flow with Dop\$3) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/05 17:34
S147	1	((affect influence) with carrier with gas with flow with Dop \$3) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/05 17:37
S148	590562	(affect influence same ("carrier gas flow") same Dop\$3) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/05 17:38
S149	3	((affect influence) same ("carrier gas flow") same Dop \$3) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/05 17:39
S150	2	S140 and (carrier near gas near flow near (high low higher lower)) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/05 17:58
S151	17	S140 and ((carrier near gas near flow) with (high low higher lower)) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/05 18:04
S152	8	S140 and ((inert near gas near flow) with (high low higher lower)) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/05 18:07

S153	1035	((inert near gas near flow) with (high low higher lower)) and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/05 18:09
S154	731	((carrier near gas near flow) with (high low higher lower)) and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/05 18:09
S155	88	S154 and ("257"/\$.ccls. or "438"/\$.ccls.)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/05 18:17
S156	731	((carrier near gas near flow) with (high low higher lower)) and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/06 09:41
S157	63	S156 and ("438"/\$.ccls.)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/06 09:41
S158	17	((carrier near gas near flow) with (high low higher lower) with dop\$3) and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/06 09:43
S159	14	438/935.ccls. and (carrier near gas near flow) and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/06 10:00
S160	17	("4745088").PN. OR ("4992301").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/06 10:05
S161	5	("2003010993").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/06 10:34
S162	0	("200310993").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/06 10:35

S163	2	("20030010993").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/06 10:35
S164	4	("2001022946").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/06 11:26
S165	1	("200122946").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/06 11:26
S166	4	("2001022946").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/06 11:26
S167	2	"6252255".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/06 11:27
S168	253	(control\$3 with growth with ((carrier inert) near2 gas)) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/06 12:06
S169	14	(control\$3 with growth with dop\$3 with ((carrier inert) near2 gas)) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/06 12:28
S170	2	("20030089300").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/06 12:37
S171	2	("20030010993").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/05/06 14:15
S172	3	((AKI RA) near2 (BANDOH)). INV.	US-PGPUB; USPAT	OR	OFF	2009/11/12 20:56

S173	0	("20030085411" "20030218179" "20040026707" "20040113166" "6091085" "6242764" "6531719" "6623998").PN.).PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/12 21:01
S174	14	("20030085411" "20030218179" "20040026707" "20040113166" "6091085" "6242764" "6531719" "6623998").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/12 21:01
S175	17	("4855249" "5122845" "5146465" "5369289" "5679152" "5862167" "5874747" "5953581" "6045626" "6091083" "6172382").PN. OR ("6623998").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/11/12 21:20
S176	16	("4855249" "5122845" "5146465" "5369289" "5862167" "5874747" "6045626" "6091083" "6172382").PN. OR ("6531719").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/11/12 21:23
S177	10	("5576637" "5687123" "5943273" "6343045" "6635934" "6657911" "6859403" "6914803" "6917556" "6999338").PN.	US-PGPUB; USPAT	OR	OFF	2009/11/12 21:26
S178	9	("20020123246" "20030070607" "20040169192" "20040206299" "20050156153" "20060046511" "20080230800" "6365921" "6555846").PN.	US-PGPUB; USPAT	OR	OFF	2009/11/12 21:27
S179	19	("5091333" "5895706" "5927995" "6010937" "6015979" "6281524").PN. OR ("6555846").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/11/12 21:34
S180	4238	(group near III near nitride near semiconductor) or (III-V near nitride near compound near semiconductor) or (GaN- based near2 semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/12 21:43
S181	99551	n-type near2 (layer or film or structure or region)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/12 21:43

S182	56743	(high\$2 near2 concentration) same (low\$2 near2 concentration)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/12 21:43
S183	39	S180 and S181 and S182 and (dislocation dis\$1location)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/12 21:43
S184	14	S183 and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/12 21:43
S185	313462	(dop\$3 impurity) with (high\$2 low\$2)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/12 21:52
S186	195526	(dop\$3 impurity) with (high\$2 low\$2)	US-PGPUB; USPAT	OR	ON	2009/11/12 21:53
S187	27347	(III near nitride) or (III \$1nitride) or (III\$1V)	US-PGPUB; USPAT	OR	OFF	2009/11/12 21:53
S188	5165	(n\$1type or n\$1dop\$3) with (Germanium Ge)	US-PGPUB; USPAT	OR	OFF	2009/11/12 21:54
S189	80194	(pit or dislocation)	US-PGPUB; USPAT	OR	OFF	2009/11/12 21:54
S190	27527	(III near nitride) or (III \$1nitride) or (III\$1V)	US-PGPUB; USPAT	OR	ON	2009/11/12 21:55
S191	27527	(III near nitride) or (III \$1nitride) or (III\$1V)	US-PGPUB; USPAT	OR	ON	2009/11/12 21:55
S192	111306	(pit or dislocation)	US-PGPUB; USPAT	OR	ON	2009/11/12 21:55
S193	5173	(n\$1type or n\$1dop\$3) with (Germanium Ge)	US-PGPUB; USPAT	OR	ON	2009/11/12 21:55
S194	1579260	stack repetition repeated perid \$2	US-PGPUB; USPAT	OR	ON	2009/11/12 21:56
S195	134	S190 and S192 and S193 and S194 and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2009/11/12 21:57
S196	68	S195 and period\$3	US-PGPUB; USPAT	OR	ON	2009/11/12 22:13
S197	1	"6091085".pn.	US-PGPUB; USPAT	OR	ON	2009/11/12 22:57
S198	85	("5373174" "5491350" "5814839" "5912477").PN. OR ("6091085").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/11/12 22:58

S199	23	("4971928" "5032893" "5040044" "5373174" "5491350" "5652434" "5779924" "5814839" "5912477" "5929467" "5962875" "6015979" "6046465" "6051849" "6091085" "6111277" "6133589" "6153010" "6229151" "6291839" "6316785" "6410942").PN. OR ("7071494").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/11/12 23:06
S200	4	((III near nitride) or (III \$1nitride) or (III\$1V) or GaN or AlGaN) same (pit or dislocation or vacancy) same (germanium or Ge) same (dop \$3 or impurity) same (layered periodic repetition stack\$2)	US-PGPUB; USPAT	OR	ON	2009/11/13 10:42
S201	0	S200 and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/13 10:42
S202	110	((III near nitride) or (III \$1nitride) or (III\$1V) or GaN or AlGaN) same (pit or dislocation or vacancy) same (dop\$3 or impurity) same (layered periodic repetition stack\$2)	US-PGPUB; USPAT	OR	ON	2009/11/13 10:43
S203	67	S202 and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/13 10:43
S204	19	("5091333" "5895706" "5927995" "6010937" "6015979" "6281524").PN. OR ("6555846").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/11/13 11:08
S205	37	("20020036286" "20020042159" "20020043890" "20030178634" "20040026704" "20040051105" "3909929" "4985113" "5332697" "5429954" "5633192" "5652438" "5717226" "5767581" "5786233" "5787104" "5804918" "5874747" "5880485" "5888886" "5900650" "5929466" "6030848" "6046464" "6090666" "6103604" "6172382"	US-PGPUB; USPAT; USOCR	OR	OFF	2009/11/13 11:23

		"6177684" "6191436" "6242328" "6261862" "6277665" "6355945" "6423984" "6429102" "6455337" "6465808").PN. OR ("6861270").URPN.				
S206	144115	(III near nitride) or (III \$1nitride) or (III\$1V) or GaN or AlGaN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/13 11:31
S207	692	S206 and (threading near2 dislocation) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/13 11:32
S208	90	S206 and (threading near2 dislocation) and ((germanium or Ge) near3 (dop\$3 impurity)) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/13 11:33
S209	6	("20010019136" "6015979" "6030848" "6232623" "6408015").PN. OR ("6764871").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/11/13 11:40
S210	2	("20040113163").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/13 11:58
S211	1	"10585744"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/13 13:11
S212	144115	(III near nitride) or (III \$1nitride) or (III\$1V) or GaN or AlGaN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/13 14:37
S213	692	S212 and (threading near2 dislocation) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/13 14:37

S214	16	S213 and (((stack\$3 period\$3) adj layer) with GaN)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/13 14:38
S215	0	S213 and (((period\$3) adj layer) with GaN)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/13 14:46
S216	5	S213 and (((period\$3) adj layer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/13 14:47
S217	19	("5185290" "5798536" "6051849" "6110277" "6121121" "6146457" "6153010" "6177359" "6274518" "6316785" "6319742" "6329667" "6355497" "6365921" "6403451" "6500257" "6582986").PN. OR ("6979584").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/11/13 14:53
S218	2	S213 and (((repetition) adj layer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/13 14:55
S219	24	("20030015708" "20030062525" "20030075728" "20040195562" "5158909" "5602418" "5622877" "5877558" "5956578" "6110277" "6255198" "6323053" "6437374" "6507041" "6515306" "6524900" "6576973" "6586777" "6586781" "6602764" "6608327" "6610995" "6617060").PN. OR ("7115896").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/11/13 15:10
S220	52	(low same (impurity concentration) same dop\$3 same high same (carrier inert) same gas same flow) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/13 18:49

S221	1	((carrier or inert) near gas near flow) with high\$3 with low\$3 with (dope impurity)) and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/13 19:06
S222	11	((carrier or inert) near gas near flow) same high\$3 same low\$3 same (dope impurity)) and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/13 19:08
S223	0	((carrier or inert) near gas near flow) near3 high\$3) same (low\$3 near4(dope impurity))) and @ad<"20040427"	US-PGPUB; USPAT	OR	OFF	2009/11/13 19:12
S224	3	((carrier or inert) near gas near flow) with high\$3) same (low\$3 with (dope impurity))) and @ad<"20040427"	US-PGPUB; USPAT	OR	OFF	2009/11/13 19:13
S225	3	((carrier or inert) near gas near flow) with high\$3) with (dope impurity)).clm. and @ad<"20040427"	US-PGPUB; USPAT	OR	OFF	2009/11/13 19:17
S226	0	((carrier or inert) near gas near flow near high\$3) with (dope impurity)).clm. and @ad<"20040427"	US-PGPUB; USPAT	OR	OFF	2009/11/13 19:19
S227	0	((carrier or inert) near gas near flow near high\$3) with (dope impurity)) and @ad<"20040427"	US-PGPUB; USPAT	OR	OFF	2009/11/13 19:19
S228	0	((carrier or inert) near gas near flow near high\$3) same (dope impurity)) and @ad<"20040427"	US-PGPUB; USPAT	OR	OFF	2009/11/13 19:20
S229	5	((carrier or inert) near gas near flow near high\$3) same (dope impurity)) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2009/11/13 19:20
S230	0	((carrier or inert) near gas near flow near high\$3) same (low near (dope impurity))) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2009/11/13 19:22
S231	2	((carrier or inert) near gas near flow) same (low near (dope impurity))) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2009/11/13 19:22
S232	8	((carrier or inert) near gas) with (low near (dope impurity))) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2009/11/13 19:23

S233	186	((carrier or inert) near gas) with (low high) with (dope impurity)) and @ad< "20040427"	US-PGPUB; USPAT	OR	ON	2009/11/13 19:26
S234	2736	((carrier or inert) near gas near flow near rate) and @ad< "20040427"	US-PGPUB; USPAT	OR	ON	2009/11/13 19:36
S235	71	S234 and (((carrier or inert) near gas near flow near rate) with higher)	US-PGPUB; USPAT	OR	ON	2009/11/13 19:37
S236	0	S234 and (((carrier or inert) near gas near flow near rate) with higher with dop\$3)	US-PGPUB; USPAT	OR	ON	2009/11/13 19:43
S237	3	S234 and (((carrier or inert) near gas) with higher with dop \$3)	US-PGPUB; USPAT	OR	ON	2009/11/13 19:44
S238	13	S234 and (((carrier or inert) near gas) with control with dop \$3)	US-PGPUB; USPAT	OR	ON	2009/11/13 19:58
S239	11283	((carrier or inert) near gas near flow) and @ad< "20040427"	US-PGPUB; USPAT	OR	ON	2009/11/14 09:42
S240	23	((carrier or inert) near gas near flow) with high with (impurity dop\$3)) and @ad< "20040427"	US-PGPUB; USPAT	OR	ON	2009/11/14 09:44
S241	3	((affect influence) same (carrier near gas near flow) same Dop\$3) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/14 11:54
S242	2	((affect influence) same (inert near gas near flow) same Dop \$3) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/14 11:56
S243	30	((carrier or inert) near flow) with (influence impact affect effect) with (impurity dop\$3)) and @ad< "20040427"	US-PGPUB; USPAT	OR	ON	2009/11/14 11:59
S244	15	((carrier or inert) near gas near flow) with (influence impact affect effect) with (impurity dop\$3)) and @ad< "20040427"	US-PGPUB; USPAT	OR	ON	2009/11/14 12:00
S245	0	((higher near (carrier or inert) near gas near flow) with (influence impact affect effect) with (impurity dop\$3)) and @ad< "20040427"	US-PGPUB; USPAT	OR	ON	2009/11/14 12:03

S246	0	((higher near (carrier or inert) near gas near flow) same (influence impact affect effect) same (impurity dop\$3)) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2009/11/14 12:03
S247	90	((carrier or inert) near gas near flow) same ((impurity dop \$3) near concentration)) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2009/11/14 12:14
S248	4	((carrier or inert) adj gas adj flow) near4 ((impurity dop\$3) adj concentration)) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2009/11/14 12:30
S249	11	((carrier or inert) adj gas adj flow) with ((impurity dop\$3) adj concentration)) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2009/11/14 12:32
S250	0	((high\$2 near2 concentration) near5 (high\$2 adj growth adj (speed rate))) same ((low\$2 near concentration) near5 (low \$2 adj growth adj (speed rate)))) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2009/11/14 14:51
S251	60	GaN same (low\$2 with growth with (speed rate)) same (high \$2 with growth with (speed rate)) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2009/11/15 13:00
S252	17	GaN same (low\$2 with growth with (speed rate)) same (high \$2 with growth with (speed rate) same different) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2009/11/15 14:15
S253	0	(GaN same (low\$2 adj concentration adj layer) same (high\$2 adj concentration adj layer) same ((Nitrogen or N2) near ratio)).clm. and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2009/11/15 18:00
S254	0	(GaN same (low\$2 adj concentration adj layer) same (high\$2 adj concentration adj layer) same ((Nitrogen or N2) near ratio)) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2009/11/15 18:00
S255	0	GaN and ((low\$2 adj concentration adj layer) same (high\$2 adj concentration adj layer) same ((Nitrogen or N2) near ratio)) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2009/11/15 18:00
S256	0	GaN and ((low\$2 adj concentration) same (high\$2 adj concentration) same ((Nitrogen or N2) near ratio)) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2009/11/15 18:03

S257	0	(GaN same (low\$2 adj concentration) same (high\$2 adj concentration) same (Nitrogen or N2)) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2009/11/15 18:10
S258	2	((GaN or III\$1N or III-V) same (low\$2 adj concentration) same (high\$2 adj concentration) same (Nitrogen or N2)) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2009/11/15 18:11
S259	26	(GaN or III\$1N or III-V) and ((low\$2 adj concentration) same (high\$2 adj concentration) same (Nitrogen or N2)) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2009/11/15 18:16
S260	1	"10585744"	US-PGPUB; USPAT	OR	ON	2009/11/15 18:26
S261	0	((((GaN or III\$1N or III-V) near4 source) with ratio) and ((low\$2 adj concentration) same (high\$2 adj concentration)) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2009/11/15 18:39
S262	12	((((GaN or III\$1N or III-V) near4 source) with ratio) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2009/11/15 18:39
S263	50	(dop\$3 with (high\$2 low\$2) with (GaN III\$1V (III near2 nitride)) with (germanium Ge)) and @ad<"20040427"	US-PGPUB; USPAT	OR	OFF	2010/04/05 14:54
S264	50	(dop\$3 with (high\$2 low\$2) with (GaN III\$1V (III near2 nitride)) with (germanium Ge)) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2010/04/05 14:54
S265	2	"11416112"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/05 16:23
S266	8	("20020123246" "20030070607" "20040169192" "20040206299" "20050156153" "20060046511" "6365921" "6555846").PN. OR ("7646027").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/04/05 16:24
S267	0	jp-11-330554	US-PGPUB; USPAT; USOCR	OR	OFF	2010/04/05 16:30
S268	0	jp-11-330554	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/04/05 16:31

S269	3	11-330554	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/04/05 16:31
S270	1383	nichia.asn. and LED	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/04/05 16:39
S271	2878	nichia.asn. and light adj emitting	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/04/05 16:40
S272	2878	nichia.asn. and light adj emitting	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/05 16:40
S273	187	nichia.asn. and (light adj emitting) and (group near III)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/05 16:41
S274	68	nichia.asn. and (light adj emitting) and (group near III) and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/05 16:41
S275	4	("20030010993" "6252255"). PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11
S276	1	"10585744"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11
S277	102492	(III near nitride) or (III \$1nitride) or (III\$1V)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11

S278	3802	(n\$1type or n\$1dop\$3) near4 (Germanium Ge)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11
S279	188674	(pit or dislocation)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11
S280	161166	dop\$3 with (high\$2 low\$2)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S281	51645	dop\$3 with (high\$2 low\$2) with (concentration density)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S282	82	S277 and S278 and S279 and S281	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S283	31	S282 and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S284	45	S279 and 257/101.ccls. and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S285	57	S279 and 257/102.ccls. and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S286	303	S279 and 257/103.ccls. and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11

S287	78	S286 and pit	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S288	21	("5091333" "5895706" "5927995" "6010937" "6015979" "6281524").PN. OR ("6555846").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/17 23:11
S289	1479	pioneer.asn. and pit	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11
S290	42	pioneer.asn. and pit and LED	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11
S291	127	dop\$3 with (high\$2 low\$2) with (GaN III\$1V) with (germanium Ge)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11
S292	56	S291 and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S293	58	(dop\$3 with (high\$2 low\$2) with (GaN III\$1V (III near2 nitride)) with (germanium Ge)) and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11
S294	102492	(III near nitride) or (III \$1nitride) or (III\$1V)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11
S295	3802	(n\$1type or n\$1dop\$3) near4 (Germanium Ge)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11

S296	188674	(pit or dislocation)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11
S297	51645	dop\$3 with (high\$2 low\$2) with (concentration density)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S298	82	S294 and S295 and S296 and S297	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S299	31	S298 and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S300	285	257/94.cor. and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S301	18	257/615.cor. and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S302	5	("20020046693" "20030070607" "20030134493" "6447604" "6773504").PN. OR ("7288830").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/17 23:11
S303	319	257/615.ccls. and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S304	3	257/e33.023.ccls. and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11

S305	8	257/e29.087.ccls. and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S306	349	257/616.ccls. and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S307	339	S306 not S303	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S308	599	high\$2 with low\$2 with dop\$3 with (germanium Ge)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S309	1468	n\$1type with (group near2 III) with nitride	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S310	105850	(pit or protrusion) near3 surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S311	0	S308 and S309 and S310 and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S312	671063	(pit or protrusion)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S313	0	S308 and S309 and S312 and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11

S314	1	S308 and S309 and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S315	5454	high\$2 same low\$2 same dop \$3 same(germanium Ge)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S316	0	S309 and S312 and S315 and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S317	15	S309 and S315 and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S318	102492	(III near nitride) or (III \$1nitride) or (III\$1V)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11
S319	3802	(n\$1type or n\$1dop\$3) near4 (Germanium Ge)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11
S320	51645	dop\$3 with (high\$2 low\$2) with (concentration density)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S321	35	S318 and S319 and pit and S320	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S322	9	S321 and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11

S323	4805	(group near III near nitride near semiconductor) or (III-V near nitride near compound near semiconductor) or (GaN-based near2 semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11
S324	105604	n-type near2 (layer or film or structure or region)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11
S325	60060	(high\$2 near2 concentration) same (low\$2 near2 concentration)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11
S326	3021	S324 same S325	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11
S327	258	S324 same ((Ge near2 dop\$3) or (dop\$3 near Ge))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11
S328	3634376	pits or holes or cavities or depressions or valley or trough or recess	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11
S329	6	S323 and S326 and S327 and S328	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11
S330	0	S329 and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S331	23	S323 and S326 and S328	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11

S332	75	S323 and S324 and S325 and S328	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11
S333	22	S332 and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S334	27008	(n-type near2 (layer or film or structure or region)) same concentration	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S335	284	S323 and S334 and S328	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S336	16	("20020123246" "20030070607" "20040169192" "20040206299" "20050156153" "20060046511" "6365921" "6555846").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S337	31	("5886367" "5927995" "6072197" "6100545" "6130446").PN. OR ("6365921").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/17 23:11
S338	26	kawano.in. and (group near III)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11
S339	0	("jp2003-017420").PN.	JPO; DERWENT	OR	OFF	2010/06/17 23:11
S340	0	("jp2003-17420").PN.	JPO; DERWENT	OR	OFF	2010/06/17 23:11
S341	0	("2003-17420").PN.	JPO; DERWENT	OR	OFF	2010/06/17 23:11
S342	4	("2003017420").PN.	JPO; DERWENT	OR	OFF	2010/06/17 23:11
S343	8	("20020053679" "20020136932" "5488233" "5740192" "6153894" "6462357" "6555846").PN. OR ("6943366").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/17 23:11

S344	2	("20040188691").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11
S345	6	("6261931").PN. OR ("6462357").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/17 23:11
S346	57923	dislocation	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11
S347	5	S323 and S326 and S327 and S346	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S348	44	S323 and S324 and S325 and (dislocation dislocation)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11
S349	14	S348 and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S350	4	(bandoh near akira).in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11
S351	2	("20040113166").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11
S352	2	"7053420".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11

S353	22	("20010050376" "20030085411" "20040048471" "5727015" "5779924" "6091083" "6091085" "6316785" "6617182" "6720586" "6940098").PN. OR ("7053420").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/17 23:11
S354	5	("20030218179" "20040113166" "6091085" "6531719" "6623998").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/17 23:11
S355	0	257/e33.033.ccls. and @ad< "20040427" and (pits or dislocation)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S356	2	257/e33.033.ccls. and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S357	3	257/e33.034.ccls. and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S358	1487	257/79.ccls. and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S359	690	257/79.cor. and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S360	116	257/79.cor. and @ad< "20040427" and (pits or dislocation)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S361	11	257/101.cor. and @ad< "20040427" and (pits or dislocation)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11

S362	11	257/102.cor. and @ad<"20040427" and (pits or dislocation)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S363	121	257/103.cor. and @ad<"20040427" and (pits or dislocation)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S364	2	("20020123246").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11
S365	37	("20020036286" "20020042159" "20020043890" "20030178634" "20040026704" "20040051105" "3909929" "4985113" "5332697" "5429954" "5633192" "5652438" "5717226" "5767581" "5786233" "5787104" "5804918" "5874747" "5880485" "5888886" "5900650" "5929466" "6030848" "6046464" "6090666" "6103604" "6172382" "6177684" "6191436" "6242328" "6261862" "6277665" "6355945" "6423984" "6429102" "6455337" "6465808").PN. OR ("6861270").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/17 23:11
S366	8	("4139858" "4862471" "5679152").PN. OR ("6103604").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/17 23:11
S367	1124	((dop\$3 impurity) with (high\$2 low\$2)) and (GaN III\$1V (III near2 nitride)) and (dop\$3 with (germanium Ge)) and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11
S368	267	S367 and (dislocation or pits)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11

S369	150	S368 and (layered stack\$2)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:11
S370	28513883	((dop\$3 impurity) with (high\$2 low\$2) with (germanium Ge)) and (GaN III\$1V (III near2 nitride)) and (layered stack\$2) and pits @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S371	12	((dop\$3 impurity) with (high\$2 low\$2) with (germanium Ge)) and (GaN III\$1V (III near2 nitride)) and (layered stack\$2) and pits and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S372	138	((dop\$3 impurity) with (high\$2 low\$2) with (germanium Ge)) and (GaN III\$1V (III near2 nitride)) and (layered stack\$2) and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:11
S373	31	((dop\$3 impurity) with (high\$2 low\$2) with (germanium Ge)) and ((GaN III\$1V (III near2 nitride)) with (resist\$3 conduct \$5)) and (layered stack\$2) and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:12
S374	72	((GaN III\$1V (III near2 nitride)) same ((germanium Ge) near4 (dop\$3 impurity)) same ((high low) and (resist\$5 conduct\$5))) and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S375	4805	(group near III near nitride near semiconductor) or (III-V near nitride near compound near semiconductor) or (GaN-based near2 semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S376	105604	n-type near2 (layer or film or structure or region)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S377	60060	(high\$2 near2 concentration) same (low\$2 near2 concentration)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12

S378	44	S375 and S376 and S377 and (dislocation dis\$1location)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S379	14	S375 and S376 and S377 and (dislocation dis\$1location) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S380	102492	(III near nitride) or (III \$1nitride) or (III\$1V)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S381	3802	(n\$1type or n\$1dop\$3) near4 (Germanium Ge)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S382	51645	dop\$3 with (high\$2 low\$2) with (concentration density)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:12
S383	35	S380 and S381 and pit and S382	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:12
S384	4576	S376 and S377 and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:12
S385	169	S384 and (dop\$3 near5 (ge Germanium))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:12
S386	6	S385 and S375	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:12

S387	5	("20030047744" "5889806" "6249534" "6252894" "6597716").PN. OR ("6822272").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/17 23:12
S388	48	S385 and (low near resistance)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:12
S389	2	"6462357".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:12
S390	6	("6261931").PN. OR ("6462357").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/17 23:12
S391	8	("20020053679" "20020136932" "5488233" "5740192" "6153894" "6462357" "6555846").PN. OR ("7172956").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/17 23:12
S392	6	("6261931").PN. OR ("6462357").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/17 23:12
S393	5	("20020046693" "20030070607" "20030134493" "6447604" "6773504").PN. OR ("7288830").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/17 23:12
S394	8	("20020123246" "20030070607" "20040169192" "20040206299" "20050156153" "20060046511" "6365921" "6555846").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/17 23:12
S395	31	("5886367" "5927995" "6072197" "6100545" "6130446").PN. OR ("6365921").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/17 23:12
S396	1	"20050104081"	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/17 23:12
S397	2	("20070029560").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S398	14	("20040211969" "20050062399" "20050224829" "20050236630" "20060273324" "20070018183" "20070170448").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12

S399	2	("20020123246").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S400	0	("(Asai near Keiichiro).in. and (III near nitride)").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S401	51	(Asai near Keiichiro).in. and (III near nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S402	51	(Asai near Keiichiro).in. and (III near nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:12
S403	256	(NGK near INSULATORS).asn. and(III near nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:12
S404	111	(NGK near INSULATORS).asn. and(III near nitride) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:12
S405	6	("20020061655" "20020155649" "20020190275" "5549951" "6508878").PN. OR ("6749957").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/17 23:12
S406	4	"2003017420"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:12
S407	306	(KAWANO near KENJI).in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:12

S408	0	(KAWANO near KENJI).in. and (III near nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:12
S409	0	(KAWANO near KENJI).in. and (GaN)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:12
S410	1	(KAWANO near KENJI).in. and Nichia	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:12
S411	1	(KAWANO near KENJI).in. and (gallium near nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:12
S412	102492	(III near nitride) or (III \$1nitride) or (III\$1V)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S413	156	S412 and ((carrier near gas) with flow with (high\$2 low\$2))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S414	102492	(III near nitride) or (III \$1nitride) or (III\$1V)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S415	59	S414 and (((("carrier gas" or "inert gas") near4 flow) with (dop\$3 impurity)) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S416	0	S414 and (((("carrier gas" or "inert gas") with flow with different) with (dop\$3 impurity)) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12

S417	96	S414 and (((("carrier gas" or "inert gas") with flow) with (dop\$3 impurity)) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S418	95	((("carrier gas" or "inert gas") same (high near2 concentration) same (low near concentration)) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S419	5	((("carrier gas" or "inert gas") same (high near2 concentration) same (low near concentration) same (flow near2 rate)) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S420	4	(effect with carrier with gas with flow with Dop\$3) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S421	1	((affect influence) with carrier with gas with flow with Dop \$3) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S422	595705	(affect influence same ("carrier gas flow") same Dop\$3) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S423	3	((affect influence) same ("carrier gas flow") same Dop \$3) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S424	2	S414 and (carrier near gas near flow near (high low higher lower)) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S425	17	S414 and ((carrier near gas near flow) with (high low higher lower)) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12

S426	8	S414 and ((inert near gas near flow) with (high low higher lower)) and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S427	1041	((inert near gas near flow) with (high low higher lower)) and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S428	732	((carrier near gas near flow) with (high low higher lower)) and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S429	88	S428 and ("257"/\$.ccls. or "438"/\$.ccls.)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S430	732	((carrier near gas near flow) with (high low higher lower)) and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S431	63	S430 and ("438"/\$.ccls.)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S432	17	((carrier near gas near flow) with (high low higher lower) with dop\$3) and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S433	14	438/935.ccls. and (carrier near gas near flow) and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S434	17	("4745088").PN. OR ("4992301").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/17 23:12
S435	5	("2003010993").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12

S436	0	("200310993").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S437	2	("20030010993").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S438	4	("2001022946").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S439	1	("200122946").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S440	4	("2001022946").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S441	2	"6252255".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S442	255	(control\$3 with growth with ((carrier inert) near2 gas)) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S443	14	(control\$3 with growth with dop\$3 with ((carrier inert) near2 gas)) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S444	2	("20030089300").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12

S445	2	("20030010993").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S446	4	((AKIRA) near2 (BANDOH)). INV.	US-PGPUB; USPAT	OR	OFF	2010/06/17 23:12
S447	0	("20030085411" "20030218179" "20040026707" "20040113166" "6091085" "6242764" "6531719" "6623998").PN.).PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S448	14	("20030085411" "20030218179" "20040026707" "20040113166" "6091085" "6242764" "6531719" "6623998").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S449	17	("4855249" "5122845" "5146465" "5369289" "5679152" "5862167" "5874747" "5953581" "6045626" "6091083" "6172382").PN. OR ("6623998").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/17 23:12
S450	17	("4855249" "5122845" "5146465" "5369289" "5862167" "5874747" "6045626" "6091083" "6172382").PN. OR ("6531719").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/17 23:12
S451	10	("5576637" "5687123" "5943273" "6343045" "6635934" "6657911" "6859403" "6914803" "6917556" "6999338").PN.	US-PGPUB; USPAT	OR	OFF	2010/06/17 23:12
S452	9	("20020123246" "20030070607" "20040169192" "20040206299" "20050156153" "20060046511" "20080230800" "6365921" "6555846").PN.	US-PGPUB; USPAT	OR	OFF	2010/06/17 23:12
S453	21	("5091333" "5895706" "5927995" "6010937" "6015979" "6281524").PN. OR ("6555846").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/17 23:12
S454	4805	(group near III near nitride near semiconductor) or (III-V near nitride near compound near semiconductor) or (GaN- based near2 semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12

S455	105604	n-type near2 (layer or film or structure or region)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S456	60060	(high\$2 near2 concentration) same (low\$2 near2 concentration)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S457	44	S454 and S455 and S456 and (dislocation dis\$1location)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S458	14	S457 and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:12
S459	327788	(dop\$3 impurity) with (high\$2 low\$2)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:12
S460	206922	(dop\$3 impurity) with (high\$2 low\$2)	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S461	29662	(III near nitride) or (III \$1nitride) or (III\$1V)	US-PGPUB; USPAT	OR	OFF	2010/06/17 23:12
S462	5622	(n\$1type or n\$1dop\$3) with (Germanium Ge)	US-PGPUB; USPAT	OR	OFF	2010/06/17 23:12
S463	84224	(pit or dislocation)	US-PGPUB; USPAT	OR	OFF	2010/06/17 23:12
S464	29861	(III near nitride) or (III \$1nitride) or (III\$1V)	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S465	29861	(III near nitride) or (III \$1nitride) or (III\$1V)	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S466	116953	(pit or dislocation)	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S467	5630	(n\$1type or n\$1dop\$3) with (Germanium Ge)	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S468	1670033	stack repetition repeated perid \$2	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S469	135	S464 and S466 and S467 and S468 and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S470	69	S469 and period\$3	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S471	1	"6091085".pn.	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12

S472	98	("5373174" "5491350" "5814839" "5912477").PN. OR ("6091085").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/17 23:12
S473	24	("4971928" "5032893" "5040044" "5373174" "5491350" "5652434" "5779924" "5814839" "5912477" "5929467" "5962875" "6015979" "6046465" "6051849" "6091085" "6111277" "6133589" "6153010" "6229151" "6291839" "6316785" "6410942").PN. OR ("7071494").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/17 23:12
S474	6	((III near nitride) or (III \$1nitride) or (III\$1V) or GaN or AlGaN) same (pit or dislocation or vacancy) same (germanium or Ge) same (dop \$3 or impurity) same (layered periodic repetition stack\$2)	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S475	0	S474 and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:12
S476	119	((III near nitride) or (III \$1nitride) or (III\$1V) or GaN or AlGaN) same (pit or dislocation or vacancy) same (dop\$3 or impurity) same (layered periodic repetition stack\$2)	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S477	67	S476 and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:12
S478	21	("5091333" "5895706" "5927995" "6010937" "6015979" "6281524").PN. OR ("6555846").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/17 23:12

S479	37	("20020036286" "20020042159" "20020043890" "20030178634" "20040026704" "20040051105" "3909929" "4985113" "5332697" "5429954" "5633192" "5652438" "5717226" "5767581" "5786233" "5787104" "5804918" "5874747" "5880485" "5888886" "5900650" "5929466" "6030848" "6046464" "6090666" "6103604" "6172382" "6177684" "6191436" "6242328" "6261862" "6277665" "6355945" "6423984" "6429102" "6455337" "6465808").PN. OR ("6861270").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/17 23:12
S480	150870	(III near nitride) or (III \$1nitride) or (III\$1V) or GaN or AlGaIn	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S481	693	S480 and (threading near2 dislocation) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:12
S482	90	S480 and (threading near2 dislocation) and ((germanium or Ge) near3 (dop\$3 impurity)) and @ad< "20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:12
S483	7	("20010019136" "6015979" "6030848" "6232623" "6408015").PN. OR ("6764871").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/17 23:12
S484	2	("20040113163").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S485	1	"10585744"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12

S486	150870	(III near nitride) or (III \$1nitride) or (III\$1V) or GaN or AlGaIn	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S487	693	S486 and (threading near2 dislocation) and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:12
S488	16	S487 and (((stack\$3 period\$3) adj layer) with GaN)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:12
S489	0	S487 and (((period\$3) adj layer) with GaN)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:12
S490	5	S487 and (((period\$3) adj layer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:12
S491	19	("5185290" "5798536" "6051849" "6110277" "6121121" "6146457" "6153010" "6177359" "6274518" "6316785" "6319742" "6329667" "6355497" "6365921" "6403451" "6500257" "6582986").PN. OR ("6979584").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/17 23:12
S492	2	S487 and (((repetition) adj layer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:12

S493	24	("20030015708" "20030062525" "20030075728" "20040195562" "5158909" "5602418" "5622877" "5877558" "5956578" "6110277" "6255198" "6323053" "6437374" "6507041" "6515306" "6524900" "6576973" "6586777" "6586781" "6602764" "6608327" "6610995" "6617060").PN. OR ("7115896").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/17 23:12
S494	52	(low same (impurity concentration) same dop\$3 same high same (carrier inert) same gas same flow) and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S495	1	((carrier or inert) near gas near flow) with high\$3 with low \$3 with (dope impurity)) and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S496	11	((carrier or inert) near gas near flow) same high\$3 same low\$3 same (dope impurity)) and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S497	0	((carrier or inert) near gas near flow) near3 high\$3) same (low\$3 near4(dope impurity))) and @ad<"20040427"	US-PGPUB; USPAT	OR	OFF	2010/06/17 23:12
S498	3	((carrier or inert) near gas near flow) with high\$3) same (low\$3 with (dope impurity))) and @ad<"20040427"	US-PGPUB; USPAT	OR	OFF	2010/06/17 23:12
S499	3	((carrier or inert) near gas near flow) with high\$3) with (dope impurity)).clm. and @ad<"20040427"	US-PGPUB; USPAT	OR	OFF	2010/06/17 23:12
S500	0	((carrier or inert) near gas near flow near high\$3) with (dope impurity)).clm. and @ad<"20040427"	US-PGPUB; USPAT	OR	OFF	2010/06/17 23:12
S501	0	((carrier or inert) near gas near flow near high\$3) with (dope impurity)) and @ad<"20040427"	US-PGPUB; USPAT	OR	OFF	2010/06/17 23:12
S502	0	((carrier or inert) near gas near flow near high\$3) same (dope impurity)) and @ad<"20040427"	US-PGPUB; USPAT	OR	OFF	2010/06/17 23:12

S503	5	((carrier or inert) near gas near flow near high\$3) same (dope impurity)) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S504	0	((carrier or inert) near gas near flow near high\$3) same (low near (dope impurity))) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S505	2	((carrier or inert) near gas near flow) same (low near (dope impurity))) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S506	8	((carrier or inert) near gas with (low near (dope impurity))) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S507	186	((carrier or inert) near gas with (low highr) with (dope impurity)) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S508	2741	((carrier or inert) near gas near flow near rate) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S509	71	S508 and ((carrier or inert) near gas near flow near rate) with higher)	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S510	0	S508 and ((carrier or inert) near gas near flow near rate) with higher with dop\$3)	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S511	3	S508 and ((carrier or inert) near gas) with higher with dop \$3)	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S512	13	S508 and ((carrier or inert) near gas) with control with dop \$3)	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S513	11307	((carrier or inert) near gas near flow) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S514	23	((carrier or inert) near gas near flow) with high with (impurity dop\$3)) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S515	3	((affect influence) same (carrier near gas near flow) same Dop\$3) and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S516	2	((affect influence) same (inert near gas near flow) same Dop \$3) and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12

S517	30	((carrier or inert) near flow) with (influence impact affect effect) with (impurity dop\$3)) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S518	15	((carrier or inert) near gas near flow) with (influence impact affect effect) with (impurity dop\$3)) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S519	0	((higher near (carrier or inert) near gas near flow) with (influence impact affect effect) with (impurity dop\$3)) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S520	0	((higher near (carrier or inert) near gas near flow) same (influence impact affect effect) same (impurity dop\$3)) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S521	90	((carrier or inert) near gas near flow) same ((impurity dop \$3) near concentration)) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S522	4	((carrier or inert) adj gas adj flow) near4 ((impurity dop\$3) adj concentration)) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S523	11	((carrier or inert) adj gas adj flow) with ((impurity dop\$3) adj concentration)) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S524	0	((high\$2 near2 concentration) near5 (high\$2 adj growth adj (speed rate))) same ((low\$2 near concentration) near5 (low \$2 adj growth adj (speed rate)))) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S525	60	GaN same (low\$2 with growth with (speed rate)) same (high \$2 with growth with (speed rate)) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S526	17	GaN same (low\$2 with growth with (speed rate)) same (high \$2 with growth with (speed rate) same different) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S527	0	(GaN same (low\$2 adj concentration adj layer) same (high\$2 adj concentration adj layer) same ((Nitrogen or N2) near ratio)).clm. and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12

S528	0	(GaN same (low\$2 adj concentration adj layer) same (high\$2 adj concentration adj layer) same ((Nitrogen or N2) near ratio)) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S529	0	GaN and ((low\$2 adj concentration adj layer) same (high\$2 adj concentration adj layer) same ((Nitrogen or N2) near ratio)) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S530	0	GaN and ((low\$2 adj concentration) same (high\$2 adj concentration) same ((Nitrogen or N2) near ratio)) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S531	0	(GaN same (low\$2 adj concentration) same (high\$2 adj concentration) same (Nitrogen or N2)) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S532	2	((GaN or III\$1N or III-V) same (low\$2 adj concentration) same (high\$2 adj concentration) same (Nitrogen or N2)) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S533	26	(GaN or III\$1N or III-V) and ((low\$2 adj concentration) same (high\$2 adj concentration) same (Nitrogen or N2)) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S534	1	"10585744"	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S535	0	((GaN or III\$1N or III-V) near4 source) with ratio) and ((low\$2 adj concentration) same (high\$2 adj concentration)) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S536	12	((GaN or III\$1N or III-V) near4 source) with ratio) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12
S537	51	(dop\$3 with (high\$2 low\$2) with (GaN III\$1V (III near2 nitride)) with (germanium Ge)) and @ad<"20040427"	US-PGPUB; USPAT	OR	OFF	2010/06/17 23:12
S538	51	(dop\$3 with (high\$2 low\$2) with (GaN III\$1V (III near2 nitride)) with (germanium Ge)) and @ad<"20040427"	US-PGPUB; USPAT	OR	ON	2010/06/17 23:12

S539	2	"11416112"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:12
S540	8	("20020123246" "20030070607" "20040169192" "20040206299" "20050156153" "20060046511" "6365921" "6555846").PN. OR ("7646027").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/17 23:12
S541	0	jp-11-330554	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/17 23:12
S542	0	jp-11-330554	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S543	4	11-330554	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S544	1391	nichia.asn. and LED	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S545	2900	nichia.asn. and light adj emitting	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/06/17 23:12
S546	2900	nichia.asn. and light adj emitting	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:12
S547	192	nichia.asn. and (light adj emitting) and (group near III)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:12

S548	68	nichia.asn. and (light adj emitting) and (group near III) and @ad<"20040427"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/17 23:12
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